### Silicon N-Channel MOS FET

# HITACHI

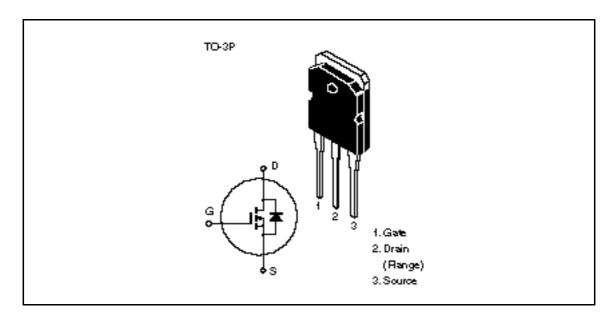
#### **Application**

High speed power switching

#### **Features**

- High breakdown voltage  $V_{DSS} = 1500 \text{ V}$
- High speed switching
- · Low drive current
- · No secondary breakdown
- · Suitable for switching regulator, DC-DC converter and motor driver

#### **Outline**





### Absolute Maximum Ratings ( $Ta = 25^{\circ}C$ )

Item	Symbol Rat		Unit	
Drain to source voltage	$V_{ t DSS}$	1500	V	
Gate to source voltage	$V_{\sf GSS}$	±20	V	
Drain current	I <sub>D</sub>	2.5	A	
Drain peak current	I *1 D(pulse)	7	Α	
Body to drain diode reverse drain current	I <sub>DR</sub>	2.5	Α	
Channel dissipation	Pch*2	100	W	
Channel temperature	Tch	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

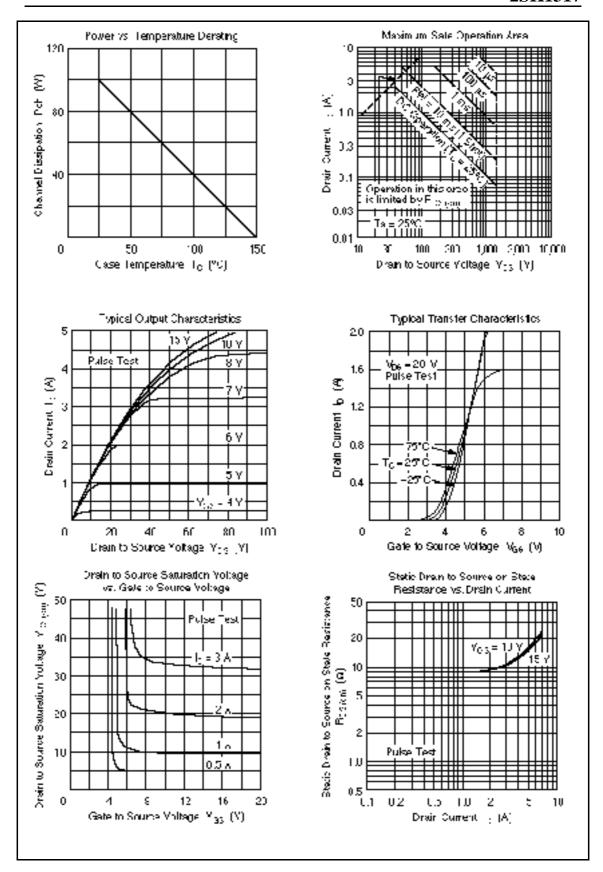
Notes: 1. PW 10 µs, duty cycle 1%

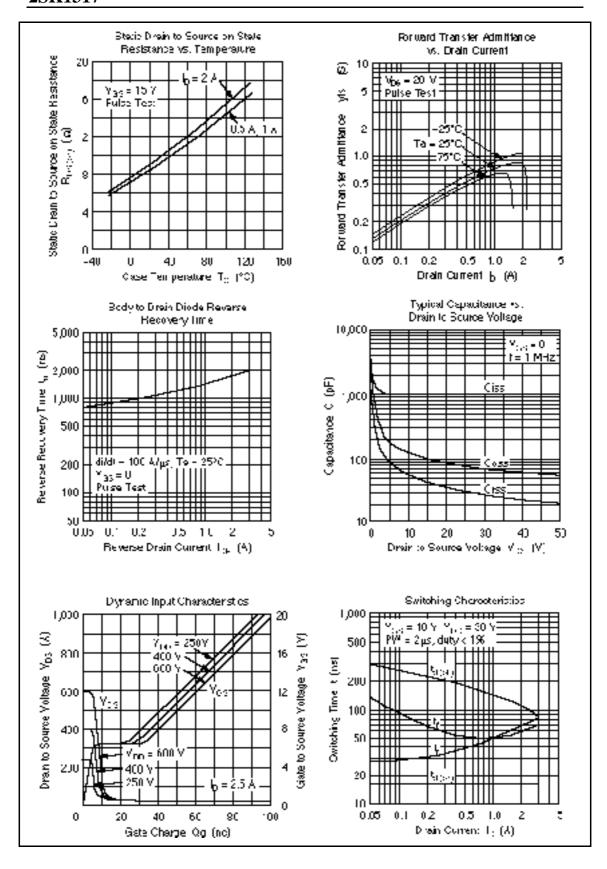
2. Value at  $T_c = 25$ °C

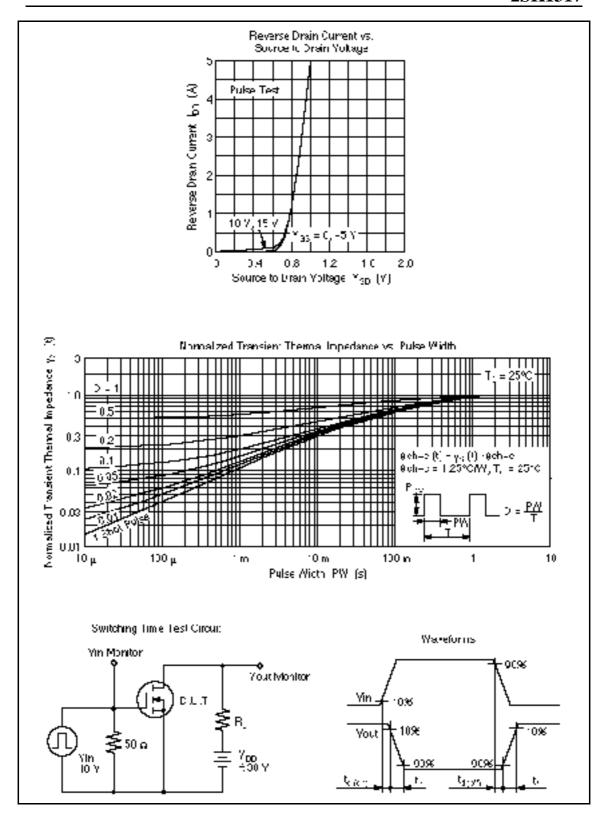
#### **Electrical Characteristics** ( $Ta = 25^{\circ}C$ )

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	1500	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±1	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	500	μΑ	$V_{DS} = 1200 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{\rm GS(off)}$	2.0	_	4.0	V	$I_{D} = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	R <sub>DS(on)</sub>	_	9	12		$I_D = 2 \text{ A}, V_{GS} = 15 \text{ V}^{*1}$
Forward transfer admittance	yfs	0.45	0.75	_	S	$I_D = 1 \text{ A}, V_{DS} = 20 \text{ V}^{*1}$
Input capacitance	Ciss	_	990	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance	Coss	_	125	_	pF	f = 1 MHz
Reverse transfer capacitance	Crss	_	60	_	pF	<del></del>
Turn-on delay time	t <sub>d(on)</sub>	_	17	_	ns	$I_D = 2 A, V_{GS} = 10 V,$
Rise time	t <sub>r</sub>	_	70	_	ns	$R_{L} = 15$
Turn-off delay time	$t_{\text{d(off)}}$	_	110	_	ns	<del></del>
Fall time	t <sub>f</sub>	_	60	_	ns	_
Body to drain diode forward voltage	$V_{DF}$	_	0.9	_	V	$I_F = 2 A, V_{GS} = 0$
Body to drain diode reverse recovery time	t <sub>rr</sub>		1750		ns	$I_F = 2 \text{ A}, V_{GS} = 0,$ $di_F/dt = 100 \text{ A/}\mu\text{s}$

Note: 1. Pulse test







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